

2SA1619, 2SA1619A

Silicon PNP epitaxial planar type

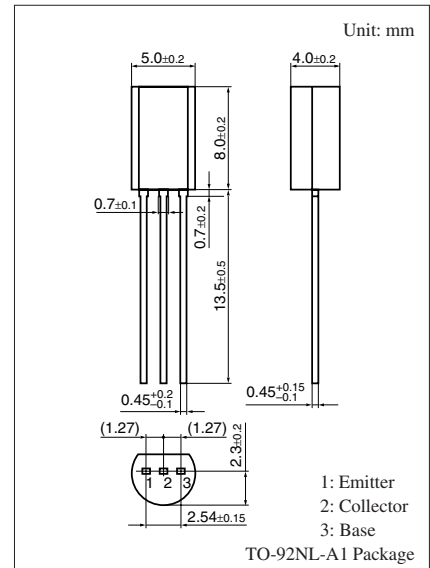
For low-frequency power amplification and driver amplification
Complementary to 2SC4208 and 2SC4208A

■ Features

- Allowing supply with the radial tapering and automatic insertion possible

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	2SA1619	-30	V
	2SA1619A	-60	
Collector-emitter voltage (Base open)	2SA1619	-25	V
	2SA1619A	-50	
Emitter-base voltage (Collector open)	V_{EBO}	-5	V
Collector current	I_C	-0.5	A
Peak collector current	I_{CP}	-1	A
Collector power dissipation	P_C	1	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$



■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

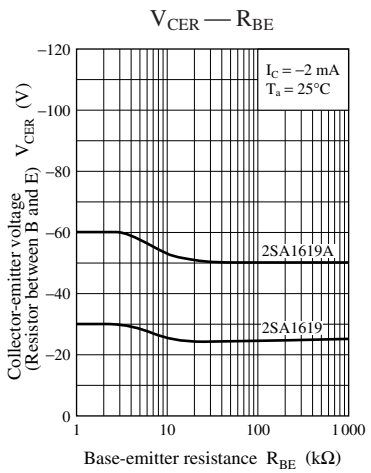
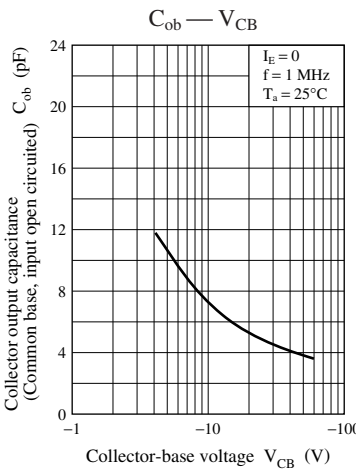
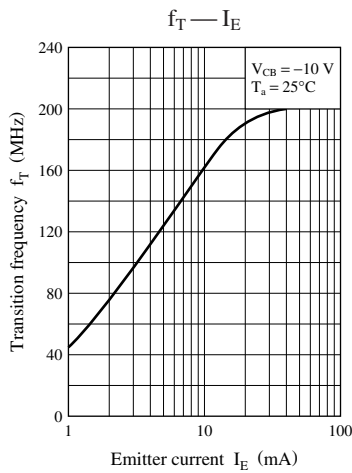
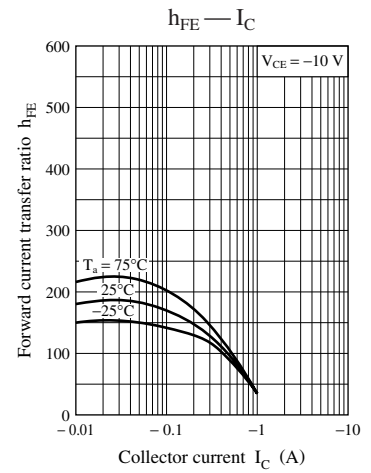
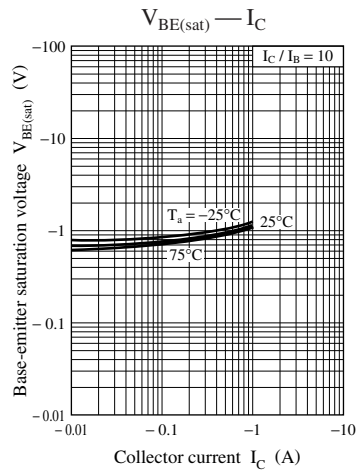
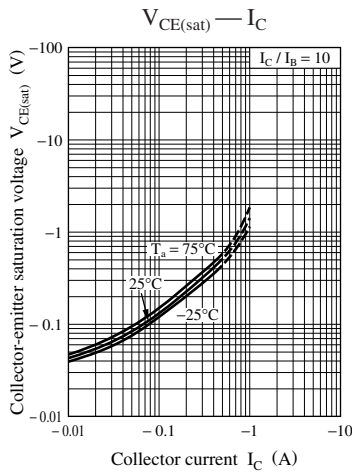
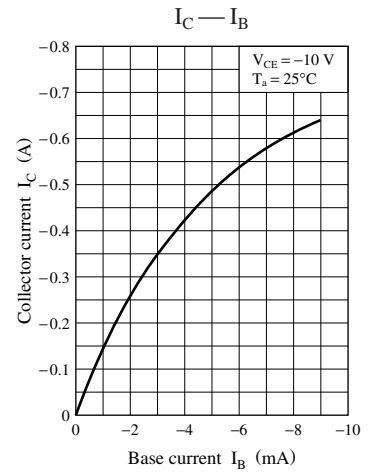
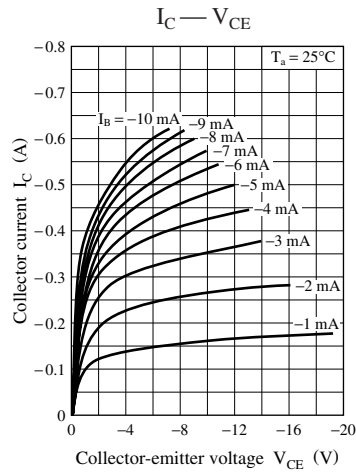
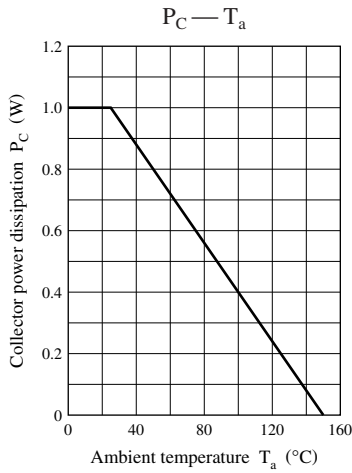
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	2SA1619	$I_C = -10 \mu\text{A}, I_E = 0$	-30			V
	2SA1619A		-60			
Collector-emitter voltage (Base open)	2SA1619	$I_C = -10 \text{mA}, I_B = 0$	-25			V
	2SA1619A		-50			
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = -10 \mu\text{A}, I_C = 0$	-5			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -20 \text{V}, I_E = 0$			-0.1	μA
Forward current transfer ratio *1	h_{FE1} *2	$V_{CE} = -10 \text{V}, I_C = -150 \text{mA}$	85	160	340	—
	h_{FE2}		$V_{CE} = -10 \text{V}, I_C = -500 \text{mA}$	40	90	
Collector-emitter saturation voltage *1	$V_{CE(sat)}$	$I_C = -300 \text{mA}, I_B = -30 \text{mA}$		-0.35	-0.60	V
Base-emitter saturation voltage *1	$V_{BE(sat)}$	$I_C = -300 \text{mA}, I_B = -30 \text{mA}$		-1.1	-1.5	V
Transition frequency	f_T	$V_{CB} = -10 \text{V}, I_E = 50 \text{mA}, f = 200 \text{MHz}$		200		MHz
Collector output capacitance (Common base, input open circuited)	C_{ob}	$V_{CB} = -10 \text{V}, I_E = 0, f = 1 \text{MHz}$		6	15	pF

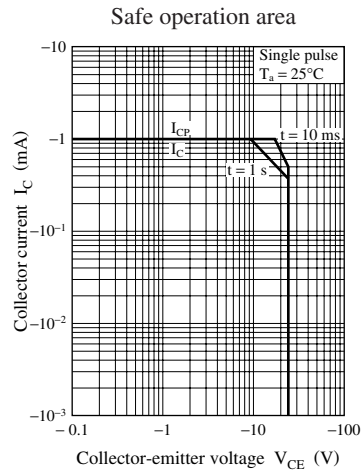
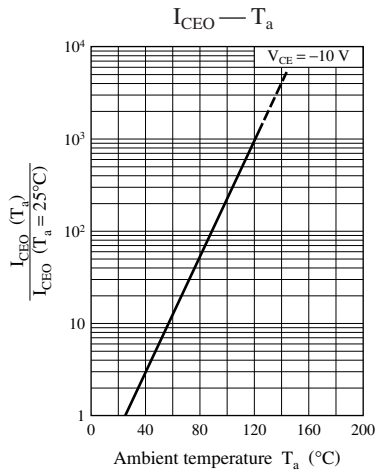
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *1: Pulse measurement

*2: Rank classification

Rank	Q	R	S
h_{FE1}	80 to 170	120 to 240	170 to 340





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